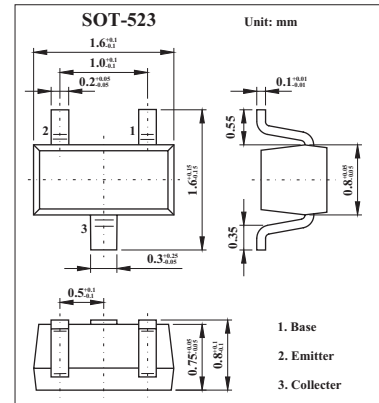


# 2SC5585

## ■ Features

- Hig current.
- Low  $V_{CE(sat)}$ :  $V_{CE(sat)} \leq 250\text{mV}$  at  $I_c=200\text{mA}/I_B=10\text{mA}$



## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	15	V
Collector-emitter voltage	$V_{CEO}$	12	V
Emitter-base voltage	$V_{EBO}$	6	V
Collector current	$I_c$	500	mA
Collector power dissipation	$P_c$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to +125	$^\circ\text{C}$

## ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_c = 10 \mu\text{A}$	15			V
Collectoe-emitter brakdown voltage	$V_{CEO}$	$I_c = 1\text{mA}$	12			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = 10 \mu\text{A}$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=15\text{V}$			100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6\text{V}$			100	nA
DC current gain	$h_{FE}$	$V_{CE}=2\text{V}, I_c=10\text{mA}$	270		680	
Collector emitter saturation voltage	$V_{CE(sat)}$	$I_c=200\text{mA}, I_B=10\text{mA}$		90	250	mV
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		7.5		pF
Transition frequency	$f_T$	$V_{CE}=2\text{V}, I_E=-10\text{mA}, f=100\text{MHz}$		320		MHz

## ■ Marking

Marking	BX
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